

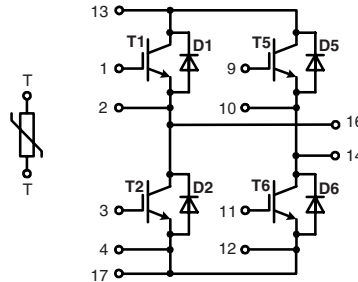
# IGBT Modules

## H-Bridge

Short Circuit SOA Capability  
 Square RBSOA

$I_{C25} = 90 \text{ A}$   
 $V_{CES} = 600 \text{ V}$   
 $V_{CE(sat) \text{ typ.}} = 2.1 \text{ V}$

Type:	NTC - Option:
MKI 75-06 A7	without NTC
MKI 75-06 A7T	with NTC



IGBTs		
Symbol	Conditions	Maximum Ratings
$V_{CES}$	$T_{VJ} = 25^{\circ}\text{C to } 150^{\circ}\text{C}$	600 V
$V_{GES}$		$\pm 20$ V
$I_{C25}$	$T_C = 25^{\circ}\text{C}$	90 A
$I_{C80}$	$T_C = 80^{\circ}\text{C}$	60 A
<b>RBSOA</b>	$V_{GE} = \pm 15 \text{ V}; R_G = 18 \Omega; T_{VJ} = 125^{\circ}\text{C}$ Clamped inductive load; $L = 100 \mu\text{H}$	$I_{CM} = 120$ A $V_{CEK} \leq V_{CES}$
$t_{SC}$ <b>(SCSOA)</b>	$V_{CE} = V_{CES}; V_{GE} = \pm 15 \text{ V}; R_G = 18 \Omega; T_{VJ} = 125^{\circ}\text{C}$ non-repetitive	10 $\mu\text{s}$
$P_{tot}$	$T_C = 25^{\circ}\text{C}$	280 W

### Features

- NPT IGBT technology
- low saturation voltage
- low switching losses
- switching frequency up to 30 kHz
- square RBSOA, no latch up
- high short circuit capability
- positive temperature coefficient for easy paralleling
- MOS input, voltage controlled
- ultra fast free wheeling diodes
- solderable pins for PCB mounting
- package with copper base plate
- UL registered, E 72873

### Advantages

- space savings
- reduced protection circuits
- package designed for wave soldering

### Typical Applications

- motor control
  - DC motor armature winding
  - DC motor excitation winding
  - synchronous motor excitation winding
- supply of transformer primary winding
  - power supplies
  - welding
  - X-ray
  - UPS
  - battery charger

Symbol	Conditions	Characteristic Values ( $T_{VJ} = 25^{\circ}\text{C}$ , unless otherwise specified)		
		min.	typ.	max.
$V_{CE(sat)}$	$I_C = 75 \text{ A}; V_{GE} = 15 \text{ V}; T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$	2.1	2.6	V
$V_{GE(th)}$	$I_C = 1.5 \text{ mA}; V_{GE} = V_{CE}$	4.5		6.5 V
$I_{CES}$	$V_{CE} = V_{CES}; V_{GE} = 0 \text{ V}; T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$	0.9		1.3 mA
$I_{GES}$	$V_{CE} = 0 \text{ V}; V_{GE} = \pm 20 \text{ V}$			200 nA
$t_{d(on)}$ $t_r$ $t_{d(off)}$ $t_f$ $E_{on}$ $E_{off}$	Inductive load, $T_{VJ} = 125^{\circ}\text{C}$ $V_{CE} = 300 \text{ V}; I_C = 75 \text{ A}$ $V_{GE} = \pm 15 \text{ V}; R_G = 18 \Omega$		50	ns
			50	ns
			270	ns
			40	ns
			3.5	mJ
			2.5	mJ
$C_{ies}$	$V_{CE} = 25 \text{ V}; V_{GE} = 0 \text{ V}; f = 1 \text{ MHz}$	3200		pF
$Q_{Gon}$	$V_{CE} = 300 \text{ V}; V_{GE} = 15 \text{ V}; I_C = 75 \text{ A}$	190		nC
$R_{thJC}$	(per IGBT)			0.44 K/W

IXYS reserves the right to change limits, test conditions and dimensions.

### Diodes

Symbol	Conditions	Maximum Ratings	
$I_{F25}$	$T_C = 25^\circ\text{C}$	140	A
$I_{F80}$	$T_C = 80^\circ\text{C}$	85	A

Symbol	Conditions	Characteristic Values		
		min.	typ.	max.
$V_F$	$I_F = 75\text{ A}; V_{GE} = 0\text{ V}; T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = 125^\circ\text{C}$	1.8 1.3	2.1	V V
$I_{RM}$ $t_{rr}$	$I_F = 60\text{ A}; di_F/dt = -500\text{ A}/\mu\text{s}; T_{VJ} = 125^\circ\text{C}$ $V_R = 300\text{ V}; V_{GE} = 0\text{ V}$	28		A
		100		ns
$R_{thJC}$	(per diode)			0.61 K/W

### Module

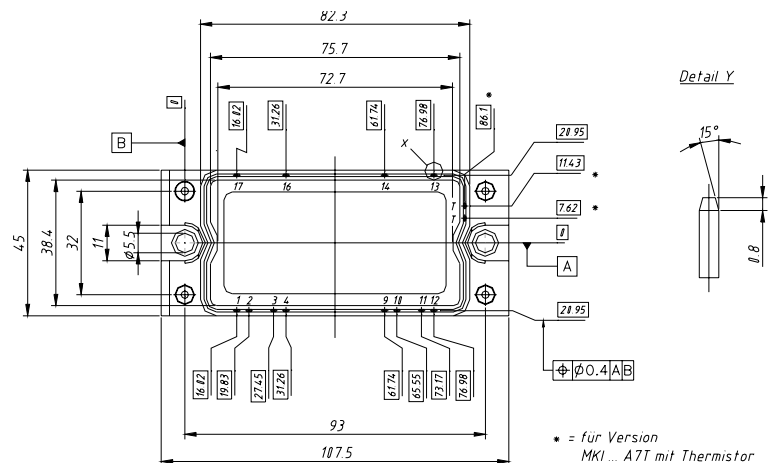
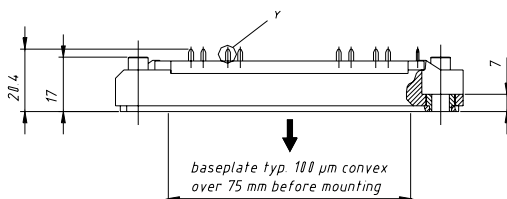
Symbol	Conditions	Maximum Ratings	
$T_{VJ}$		-40...+150	$^\circ\text{C}$
$T_{stg}$		-40...+125	$^\circ\text{C}$
$V_{ISOL}$	$I_{ISOL} \leq 1\text{ mA}; 50/60\text{ Hz}$	2500	V~
$M_d$	Mounting torque (M5)	2.7 - 3.3	Nm

Symbol	Conditions	Characteristic Values		
		min.	typ.	max.
$R_{pin-chip}$			5	m $\Omega$
$d_s$	Creepage distance on surface	6		mm
$d_A$	Strike distance in air	6		mm
$R_{thCH}$	with heatsink compound		0.02	K/W
Weight			180	g

### Temperature Sensor NTC

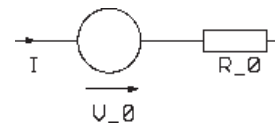
Symbol	Conditions	Characteristic Values		
		min.	typ.	max.
$R_{25}$	$T = 25^\circ\text{C}$	4.75	5.0	5.25 k $\Omega$
$B_{25/50}$			3375	K

Dimensions in mm (1 mm = 0.0394")



### Equivalent Circuits for Simulation

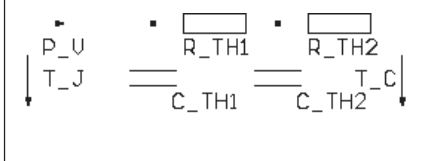
#### Conduction



IGBT (typ. at  $V_{GE} = 15\text{ V}; T_J = 125^\circ\text{C}$ )  
 $V_0 = 0.95\text{ V}; R_0 = 20\text{ m}\Omega$

Free Wheeling Diode (typ. at  $T_J = 125^\circ\text{C}$ )  
 $V_0 = 1.014\text{ V}; R_0 = 4\text{ m}\Omega$

#### Thermal Response



IGBT (typ.)  
 $C_{th1} = 0.248\text{ J/K}; R_{th1} = 0.343\text{ K/W}$   
 $C_{th2} = 1.849\text{ J/K}; R_{th2} = 0.097\text{ K/W}$

Free Wheeling Diode (typ.)  
 $C_{th1} = 0.23\text{ J/K}; R_{th1} = 0.483\text{ K/W}$   
 $C_{th2} = 1.3\text{ J/K}; R_{th2} = 0.127\text{ K/W}$

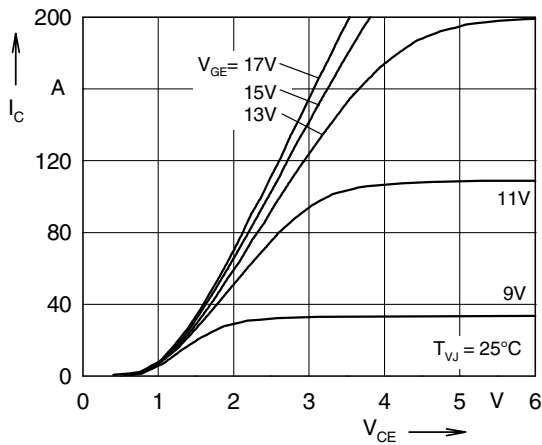


Fig. 1 Typ. output characteristics

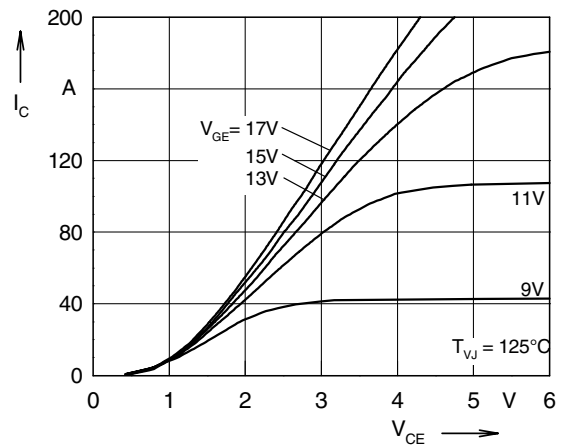


Fig. 2 Typ. output characteristics

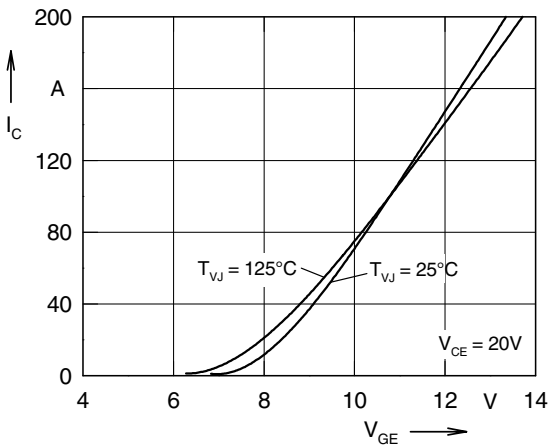


Fig. 3 Typ. transfer characteristics

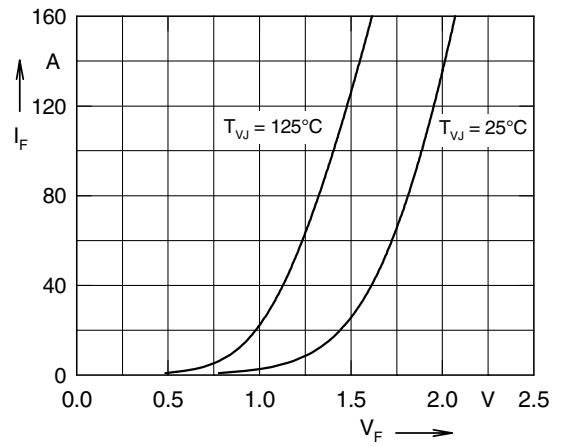


Fig. 4 Typ. forward characteristics of free wheeling diode

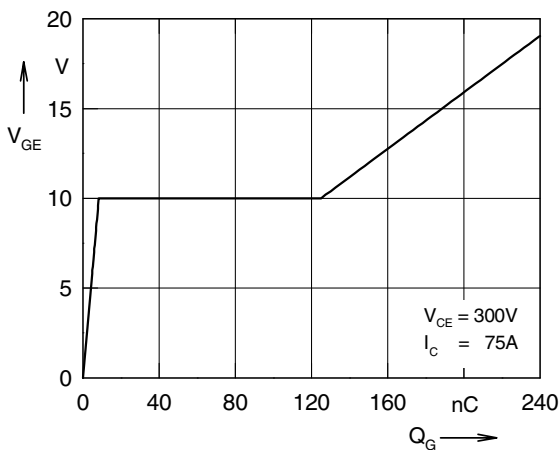


Fig. 5 Typ. turn on gate charge

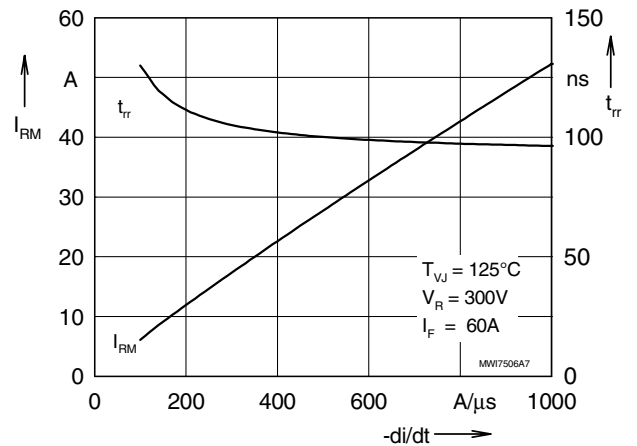


Fig. 6 Typ. turn off characteristics of free wheeling diode

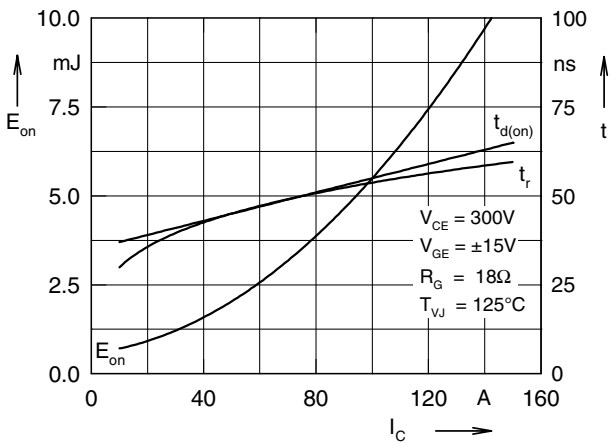


Fig. 7 Typ. turn on energy and switching times versus collector current

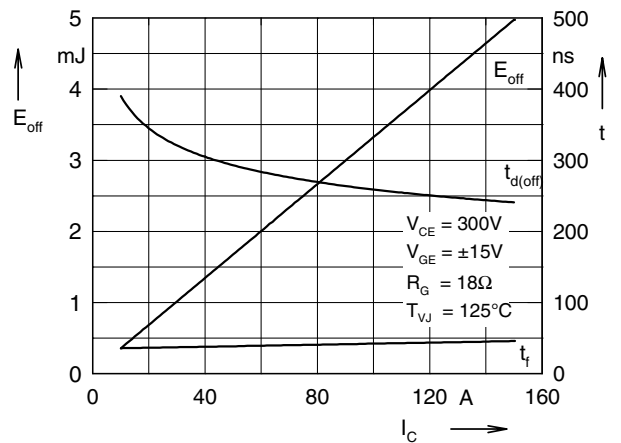


Fig. 8 Typ. turn off energy and switching times versus collector current

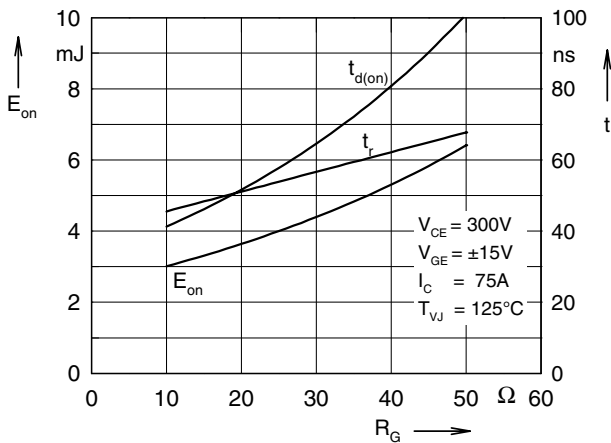


Fig. 9 Typ. turn on energy and switching times versus gate resistor

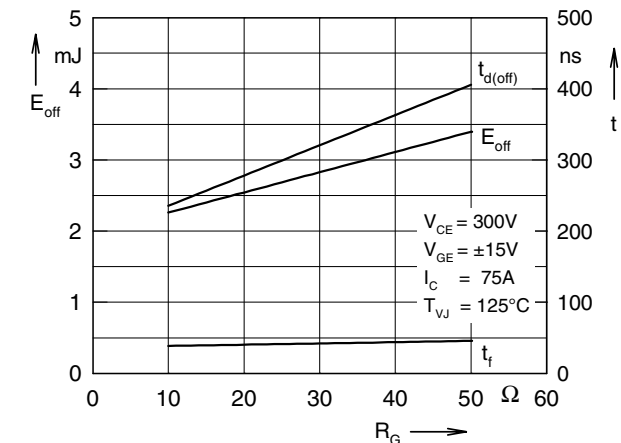


Fig. 10 Typ. turn off energy and switching times versus gate resistor

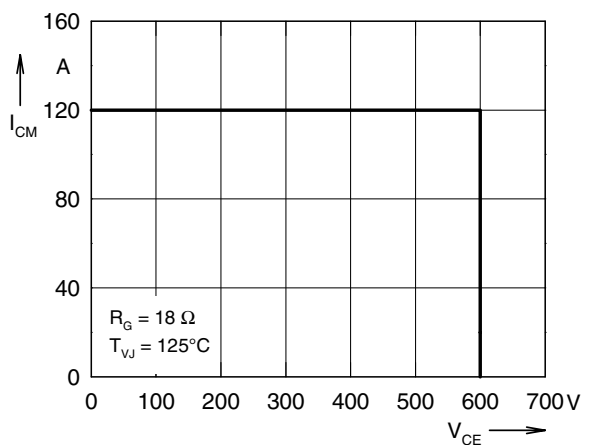


Fig. 11 Reverse biased safe operating area RBSOA

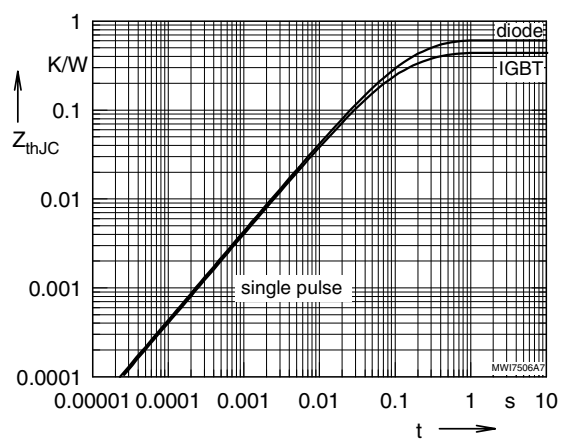


Fig. 12 Typ. transient thermal impedance